

PD1300-35D32-I
Φ5 Stem Type InGaAs PIN-Photodiode

PD1300-35D32-I is InGaAs PIN-Photodiode featuring excellent responsibility and high photocurrent for near infrared.

This PIN-Photodiode consists of a large chip with 0.35x0.35mm active area mounted on the TO-18 stem and is hermetical sealed by metal can with glass ball lens.

These devices are designed to be high photocurrent gains with an angle of half sensitivity of ±15°.

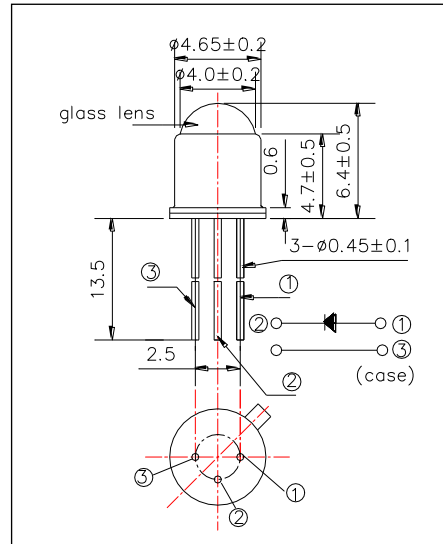
<Features>

- High Reliability
- High Response

<Specifications>

1. Product Name: InGaAs PIN-Photodio
2. Type Number: PD1300-35D32-I
3. Chip:
 - Active Area: 0.35mm x0.35mm
4. Package
 - Type: TO-18 (3pins)
 - Lens: Glass Ball Lens
 - Cap: Gold Plated

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	VR	15	V
Operating Temperature	TOPR	-20 ~ +90	°C
Storage Temperature	TSTG	-30 ~+100	°C
Soldering Temperature*	TSOL	265	°C

* Soldering condition must be completed within 3 seconds at 265°C

Electro-Optical Characteristics [Ta=25°C typ.]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Photo Responsibility	RE	VR=0V, λP =1300nm		0.9		A/W
Photo Current*	IL	VR=0V, λP =1300nm	26			μA
Dark Current	ID	VR=3V			100	nA
Spectral Responsibility(Peak)	λP	VR=0V	1000		1600	nm
Half Angle of Sensitivity	θ1/2	VR=0V		± 15		deg
Total Capacitance	CT	F=1MHz	VR=0V	50		pF
			VR=5V	15		
Rise/Fall Time(10%~90%)	tr	RL=1kΩ, VR=1V		10		ns
	tf			5		

* Measured by Epitex's calibrated tool

